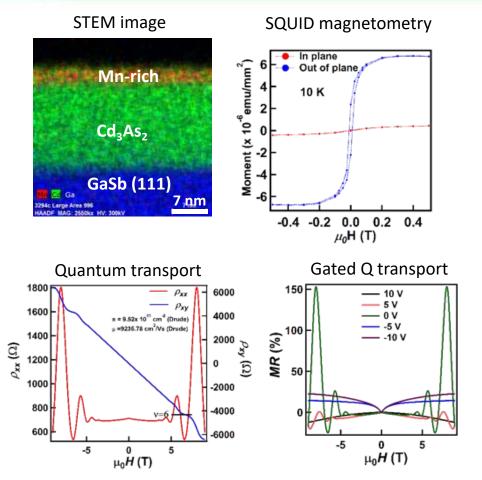
Interfacing a Dirac semimetal with magnetism Institute for Quantum Matter EFRC DE-SC0019331



R. Xiao, A. Mitra, W. Yanez, Y. Fang, J. Held, J. Chamorro, A. Mkhoyan, T. McQueen, B. Ramshaw, N. Samarth, in preparation

IQM-EFRC research performed at Cornell , Penn State, and Johns Hopkins as part of the topological superconductivity thrust.



Office of Science

Scientific Achievement

We have measured Fermi-energy-dependent quantum transport in electrostatically-gated thin films of the Dirac semimetal Cd₃As₂ interfaced with a ferromagnet.

Significance and Impact

Introducing magnetism into a Dirac semimetal breaks time-reversal symmetry and is an important step along the path to realizing a monopole superconductor.

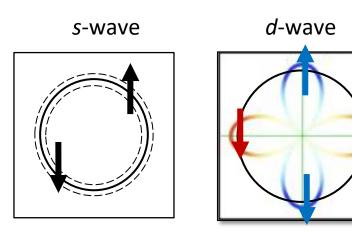
Research Details

- MBE growth of Mn-Cd₃As₂ on (111) GaSb
- Mn-dopant acts a surfactant, segregating near surface in a ferromagnetic phase with out-of-plane magnetic anisotropy.
- Quantum transport in Cd₃As₂ remains intact and is studied as function of Fermi energy.



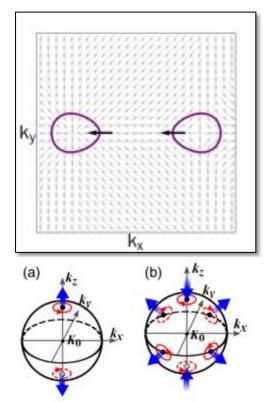
Monopole superconductors are classified by topology

Conventional



Conventional superconductors are classified by the point-group symmetry of the Cooper pairs

Monopole

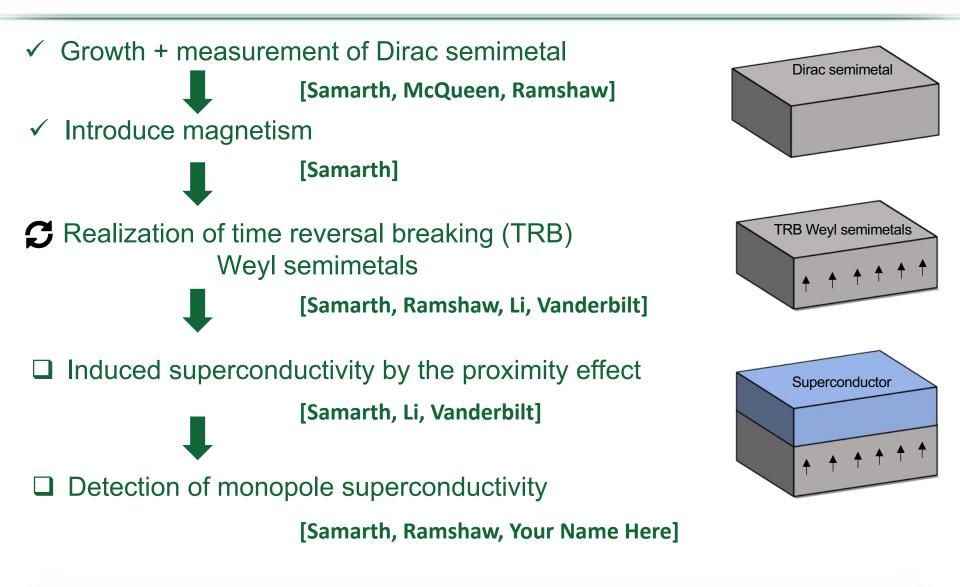


Nodal structure enforced by topology of bands, not by symmetry of pairing.

Theory [Li]

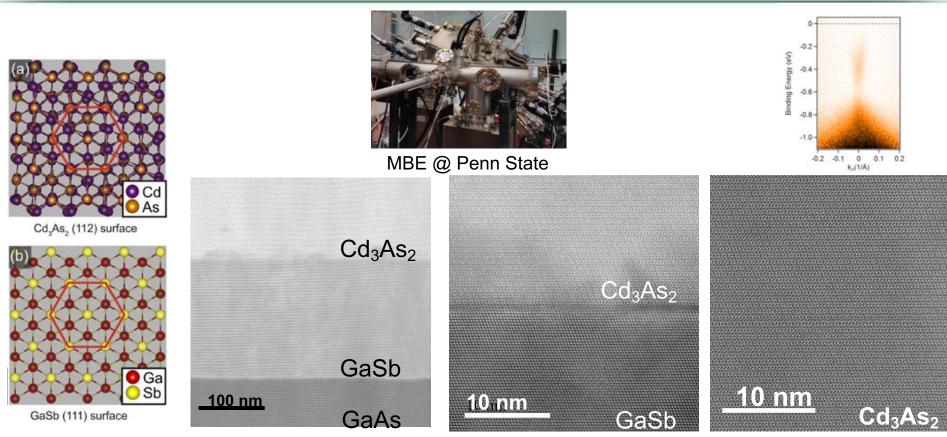


Thin-films as a flexible platform





MBE growth and characterization of Cd₃As₂



For prior work: see T. Schumann, *et.al.*, APL Mater. 4, 126110 (2016)

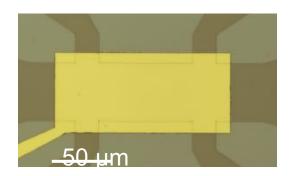
 Cd_3As_2 is grown on GaAs(111) substrate with a GaSb buffer layer.

In vacuo ARPES (preliminary) consistent with prior results on cleaved bulk crystals.

Synthesis [Samarth, McQueen] Theory [Vanderbilt, Li]



High quantum mobility, tunable carrier density



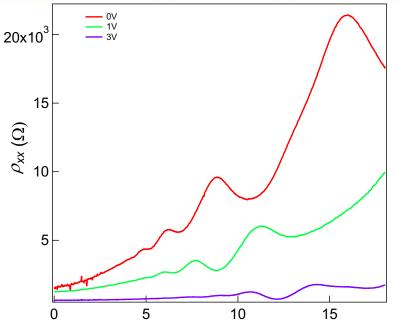
Transport devices: Photolithography + Ar etching Electrostatic top gate via ALD of Al_2O_3 (dielectric) + Ti/Au electrode.

Quantum transport measurements: Cornell: B < 20 T, T > 270 mK PSU: B < 8 T, T > 2 K

Typical Drude mobility in range 2200 – 6000 cm²/V.s

Measurements [Ramshaw, Samarth]



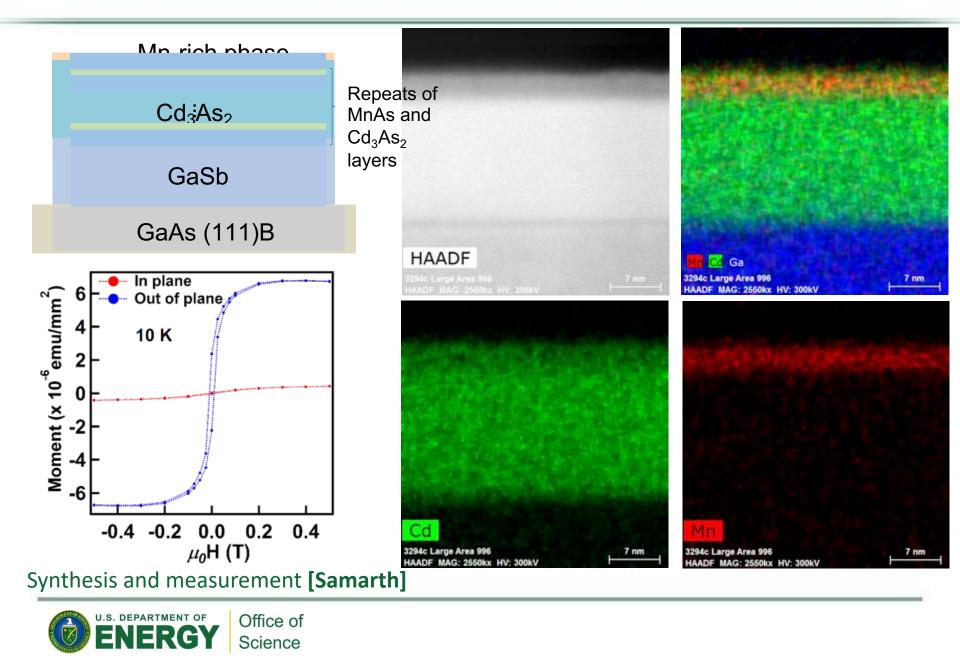


 $\mu_0 H(T)$

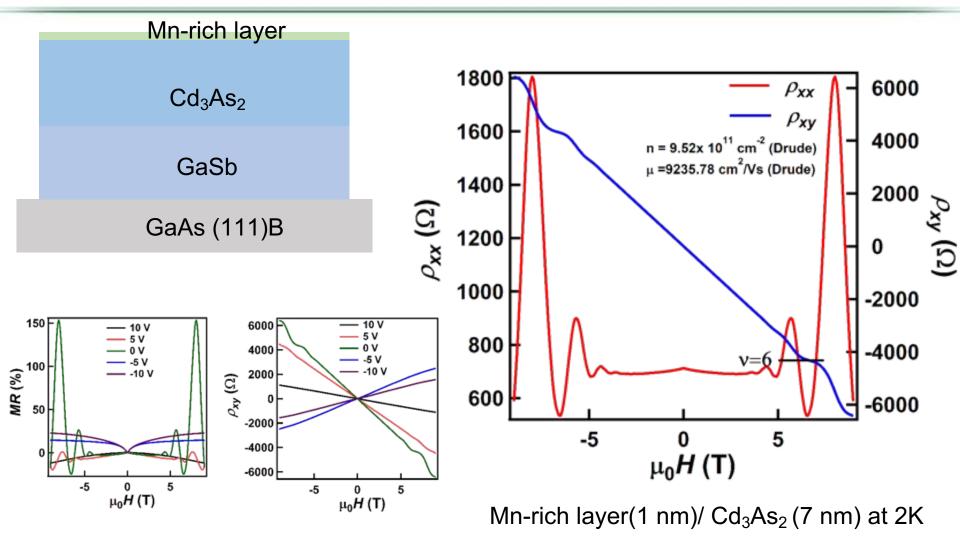
Gate (V)	Frequency (T)	3D carrier density (cm-3)		-
0	20.5	1.04E+18		
1	25.70			
3	41.13	2.97E+18	4.46E+12	2241.77

15 nm thick Cd₃As₂ sample

Introduction of magnetism into Cd₃As₂



High mobility is retained (improved!) in Mn-capped samples



Measurement [Samarth]



The next steps

- Second approach to magnetism: growth on the magnetic semiconductor (Ga,Mn)Sb. [Samarth]
- Use Cd₃As₂ source (rather than separate Cd and As) to control vacancies and improve mobility. [McQueen]
- High-field angle dependence to determine whether carriers are 2D or 3D, Berry phase. 20 tesla continuous rotation, 35 tesla pulsed in-house. [Ramshaw]
- Determine electronic structure in magnetically doped samples.
 [Li, Vanderbilt]
- Introduction of superconductivity and detection of topologically enforced nodal quasiparticles with 3ω thermal transport and penetration depth. [Samarth, Ramshaw,...]



